

SUBSTRATE PROPERTY	MGSi4MCZNA _s	MGSi4MCZNS _b	MGSi4MCZNP	MGSi4MCZPB
Diameter	100 mm			
Growth Method	MCZ			
Orientation	<100>, <110>, <111>			
Carrier Type	N-type			P-type
Dopant	As	Sb	P	B
Resistivity	100-1000 Ω·cm			
Thickness	525 μm ± 25 μm			
TTV	≤10 μm			
Bow	≤40 μm			

*The other specifications can be customized according to customer's requirements